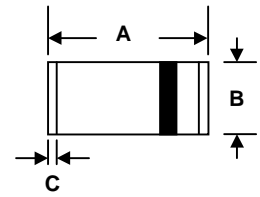


**Silicon Epitaxial Planar Switching Diode**

Fast switching diode in MiniMELF case especially suited for automatic surface mounting.  
 Identical electrically to standard 1N4448.



MiniMELF		
Dim	Min	Max
A	3.30	3.60
B	1.40	1.50
C	0.25	0.33
All Dimensions in mm		

**Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )**

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	$V_R$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current at $t < 1\text{ s}$	$I_{FSM}$	500	mA
Power Dissipation	$P_{tot}$	500 <sup>1)</sup>	mW
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

<sup>1)</sup> Valid provided that electrodes are kept at ambient temperature.

**Characteristics at  $T_a = 25\text{ }^\circ\text{C}$**

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 5\text{ mA}$ at $I_F = 100\text{ mA}$	$V_F$	0.62 -	0.72 1	V
Reverse Leakage Current at $V_R = 20\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 20\text{ V}, T_j = 150\text{ }^\circ\text{C}$	$I_R$ $I_R$ $I_R$	- - -	25 5 50	nA $\mu\text{A}$ $\mu\text{A}$
Reverse Breakdown Voltage at $I_R = 100\text{ }\mu\text{A}$	$V_{(BR)R}$	100	-	V
Capacitance at $V_R = 0, f = 1\text{ MHz}$	$C_{tot}$	-	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}, V_R = 6\text{ V}, R_L = 100\text{ }\Omega$	$t_{rr}$	-	4	ns

